



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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## Features & Benefits

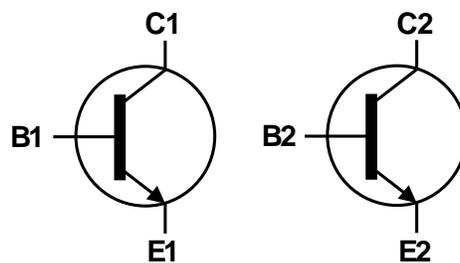
- $BV_{CEO} > 80V$
- $I_{CM} = 1A$  Peak Pulse Current
- General purpose NPN transistors ideally suited for low power amplification and switching applications
- Dual transistors in a single SOT26 package taking half the footprint of two equivalent transistors in SOT23
- Epitaxial Planar Die Construction

## Mechanical Data

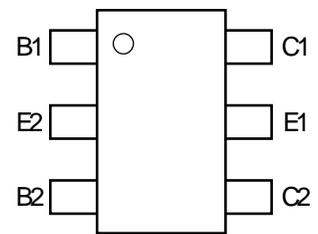
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.015 grams (Approximate)



Top View



Device Symbol



Top View  
Pin-Out

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	I <sub>C</sub>	500	mA
Peak Pulse Collector Current	I <sub>CM</sub>	1	A

### Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

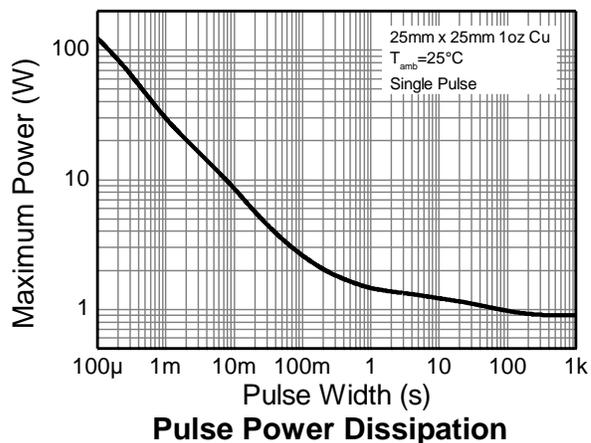
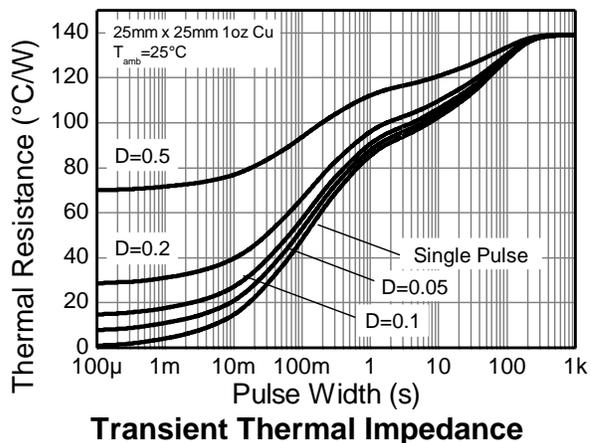
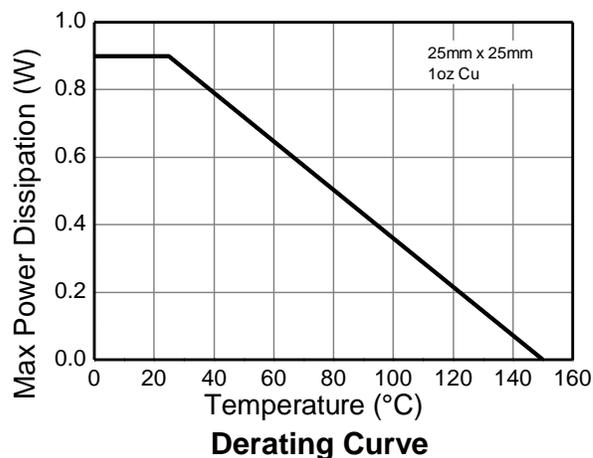
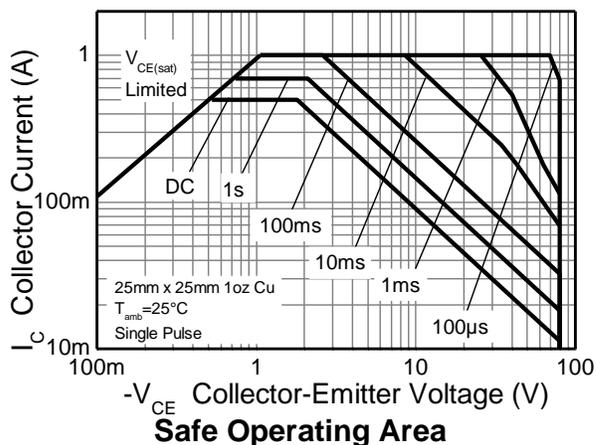
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P <sub>D</sub>	1.28	W
		10.3	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	0.90	mW/°C
		7.14	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	97	°C/W
		140	
Thermal Resistance, Junction to Lead	R <sub>θJL</sub>	103	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as Note 5, except the device is measured at t ≤ 5 seconds.
  - For a dual device with one active die.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

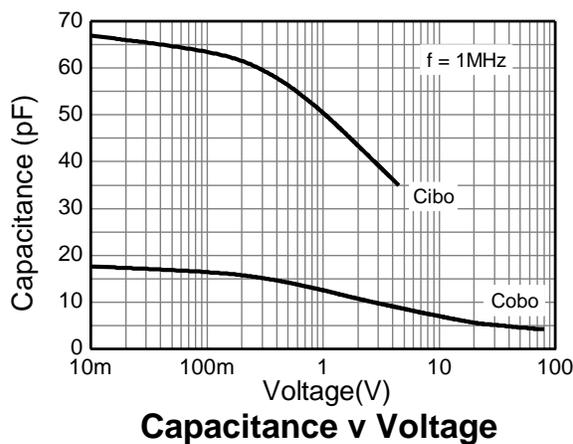
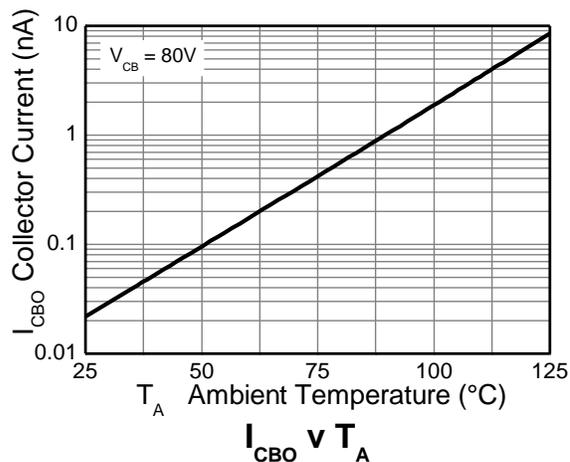
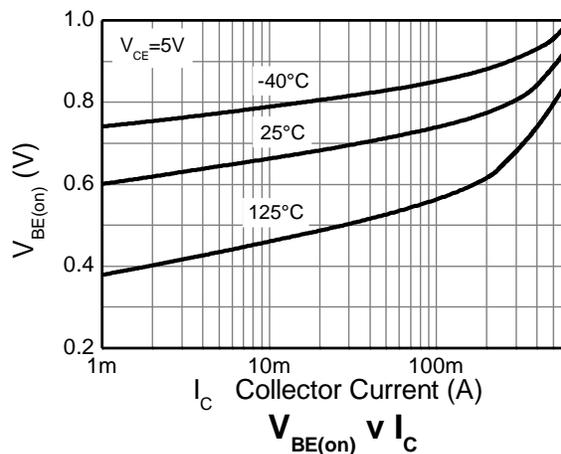
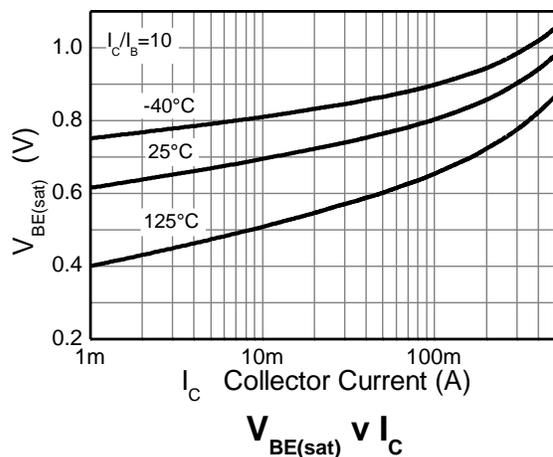
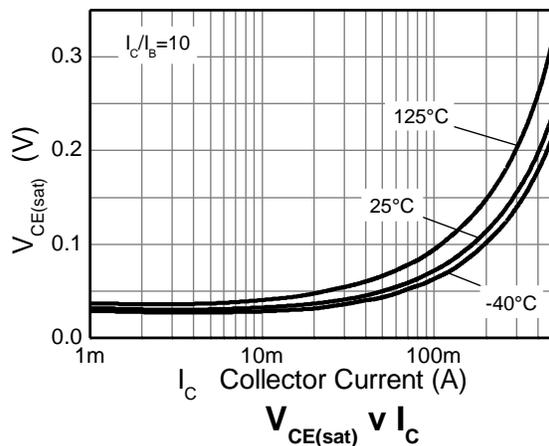
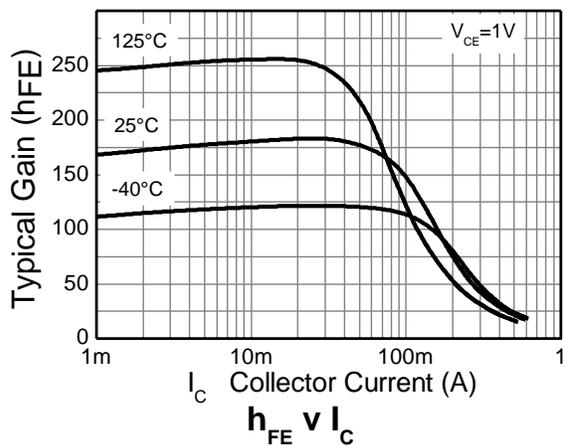


**Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

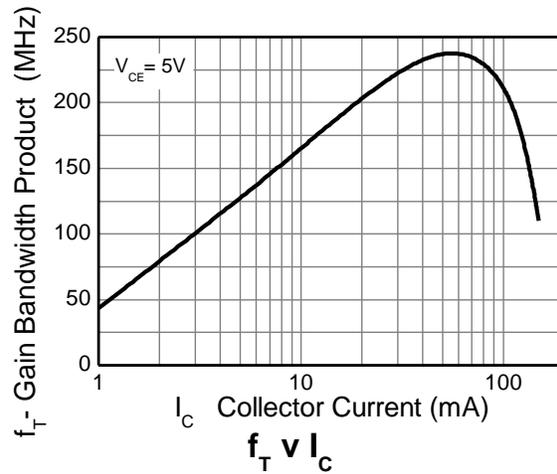
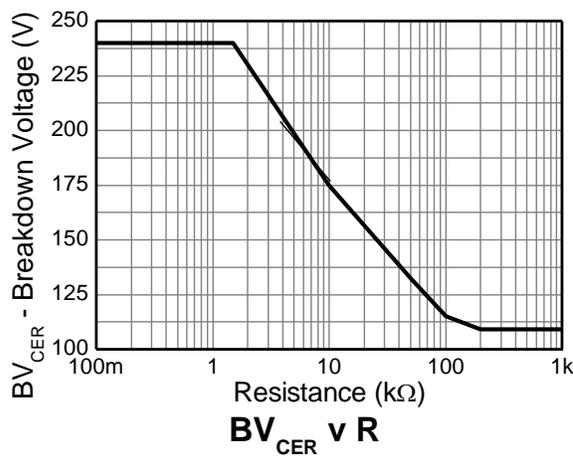
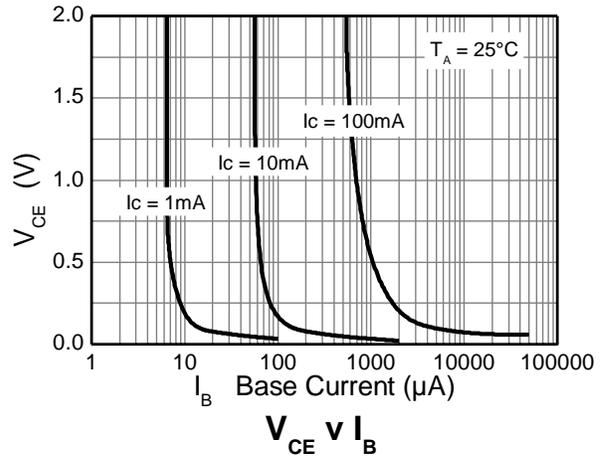
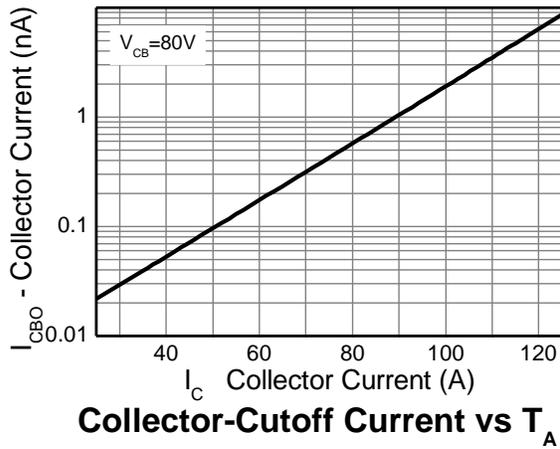
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	100	—	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	80	—	—	V	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	—	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
Collector-Base Cut-Off Current	I <sub>CBO</sub>	—	—	100	nA	V <sub>CB</sub> = 80V, I <sub>E</sub> = 0
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	—	—	100	nA	V <sub>CE</sub> = 80V, I <sub>B</sub> = 0
Emitter-base Cut-Off Current	I <sub>EBO</sub>	—	—	100	nA	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS (Note 10)</b>						
DC Current Gain	h <sub>FE</sub>	100	—	—	—	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1V
		100	—	—		I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	—	0.25	V	I <sub>C</sub> = 100mA, I <sub>B</sub> = 10mA
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>	—	—	1.20	V	I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1V
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Current Gain-Bandwidth Product	f <sub>T</sub>	100	163	—	MHz	V <sub>CE</sub> = 2V, I <sub>C</sub> = 10mA, f = 100MHz
Output Capacitance	C <sub>obo</sub>	—	7	—	pF	V <sub>CB</sub> = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

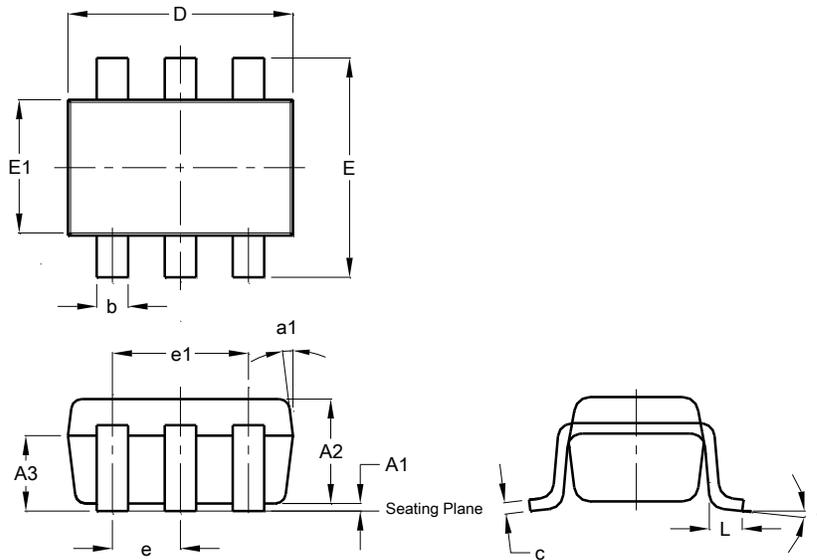
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)



**Typical Electrical Characteristics – Continued** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)

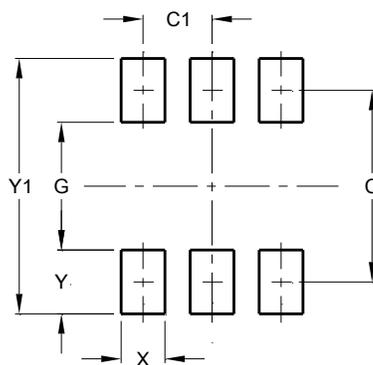


## Package Outline



SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	-	-	0.95
e1	-	-	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	-	-	8°
a1	-	-	7°
<b>All Dimensions in mm</b>			

## Suggested Pad Layout



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20